

TOSHIBA BIPOLAR DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TD62593AFN, TD62594AFN, TD62597AFN, TD62598AFN**8ch SINGLE DRIVER : COMMON Emitter**

The TD62593, 4, 7, 8AFN are comprised of eight NPN Transistor Arrays.

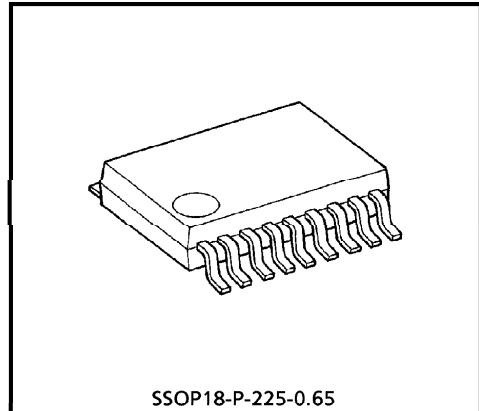
Applications include relay, hammer, lamp and display (LED) drivers.

FEATURES

- Package Type : SSOP18pin
- High Sustaining Voltage Output : 50V (MIN.)
- Low Saturation Voltage : $V_{CE}(\text{sat}) = 0.8V$
@ $I_{OUT} = 150\text{mA}$ Inputs Compatible with Various type Logic.

TD62593AFN, TD62597AFN : $R_{IN} = 2.7\text{k}\Omega$ TTL, 5V CMOS

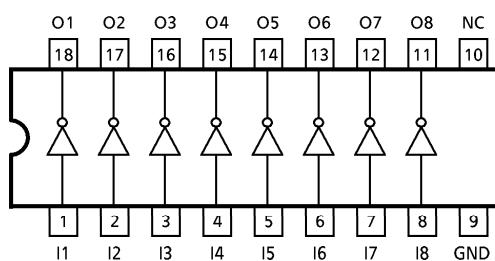
TD62594AFN, TD62598AFN : $R_{IN} = 10.5\text{k}\Omega$ 6~15V PMOS, CMOS



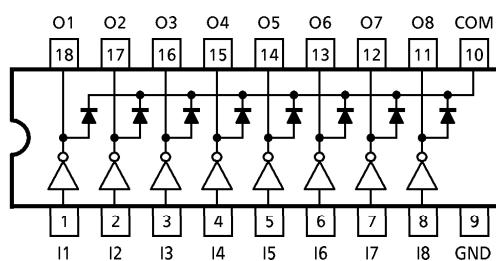
Weight : 0.09g (Typ.)

PIN CONNECTION (TOP VIEW)

TD62593AFN, TD62594AFN



TD62597AFN, TD62598AFN

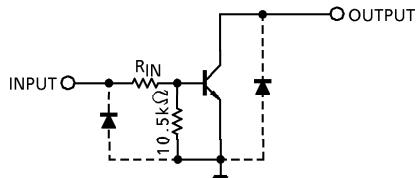


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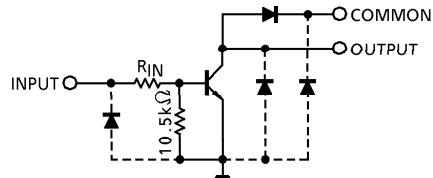
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SCHEMATICS (EACH DRIVER)

TD62593AFN, TD62594AFN

TD62593AFN $R_{IN} = 2.7\text{k}\Omega$ TD62594AFN $R_{IN} = 10.5\text{k}\Omega$

TD62597AFN, TD62598AFN

TD62597AFN $R_{IN} = 2.7\text{k}\Omega$ TD62598AFN $R_{IN} = 10.5\text{k}\Omega$

Note : The input and output parasitic diodes cannot be used as clamp diodes.

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V_{CEO}	50	V
Collector-Base Voltage	V_{CBO}	50	V
Clamp Diode Reverse Voltage	V_R *1	50	V
Collector Current	I_C	200	mA / ch
Input Voltage	V_{IN}	- 0.5~30	V
Power Dissipation	P_D *2	0.96	W
Operating Temperature	T_{opr}	- 40~85	$^\circ\text{C}$
Storage Temperature	T_{stg}	- 55~150	$^\circ\text{C}$

*1 : Except TD62593AFN, TD62594AFN

*2 : On Glass Epoxy PCB (50 × 50 × 1.6mm Cu 40%)

RECOMMENDED OPERATING CONDITIONS ($T_a = - 40\sim 85^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Voltage	V_{CEO}		0	—	50	V
Collector-Base Voltage	V_{CBO}		0	—	50	V
Collector Current	I_C		0	—	150	mA / ch
Clamp Diode Reverse Voltage	V_R *1		7	—	50	V
Input Voltage	V_{IN}		0	—	25	V
Input Current	I_{IN}		0	—	10	mA
Input Voltage (Output On)	TD62593AFN	V_{IN} (ON)	2.4	—	25	V
	TD62597AFN		7.0	—	25	
Power Dissipation	P_D *2		—	—	0.4	W

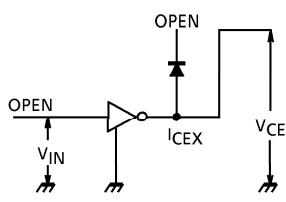
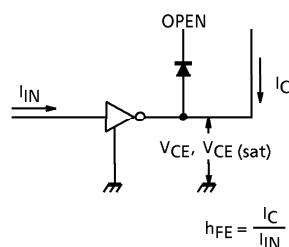
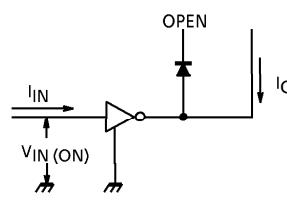
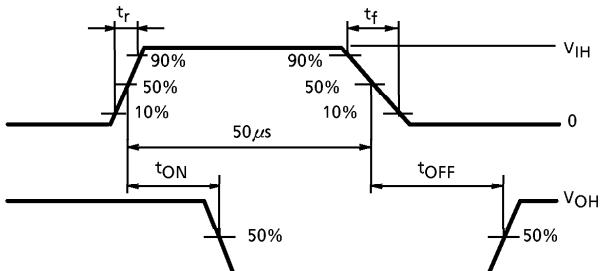
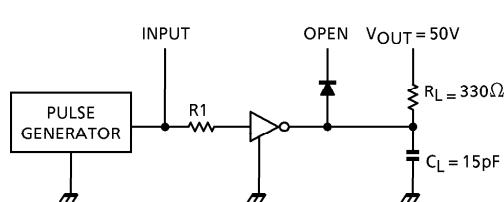
*1 : Except TD62593AFN, TD62594AFN

*2 : On Glass Epoxy PCB (50 × 50 × 1.6mm Cu 40%)

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Leakage Current	I_{CEX}	1	$V_{CE} = 50\text{V}, V_{IN} = 0$	—	—	10	μA
Output Saturation Voltage	$V_{CE} (\text{sat})$	2	$I_C = 10\text{mA}, I_{IN} = 0.4\text{mA}$	—	—	0.2	V
			$I_C = 150\text{mA}, I_{IN} = 3.0\text{mA}$	—	—	0.8	
DC Current Transfer Ratio	h_{FE}	2	$V_{CE} = 10\text{V}, I_C = 10\text{mA}$	50	—	—	
Input Current	TD62593AFN TD62597AFN	$I_{IN} (\text{ON})$	$V_{IN} = 2.4\text{V}, I_C = 50\text{mA}$	—	—	0.9	mA
	TD62594AFN TD62598AFN			—	—	0.9	
Turn-On Delay	t_{ON}	4	$V_{OUT} = 50\text{V}, R_L = 330\Omega$	—	0.1	—	μs
Turn-Off Delay	t_{OFF}			—	3.0	—	

TEST CIRCUIT

1. I_{CEX} 2. $h_{FE}, V_{CE} (\text{sat})$ 3. $I_{IN} (\text{ON})$ 4. t_{ON}, t_{OFF} 

(Note 1) Pulse Width $50\mu\text{s}$, Duty Cycle 10%
Output Impedance 50Ω , $t_r \leq 5\text{ns}$, $t_f \leq 10\text{ns}$

(Note 2) See below

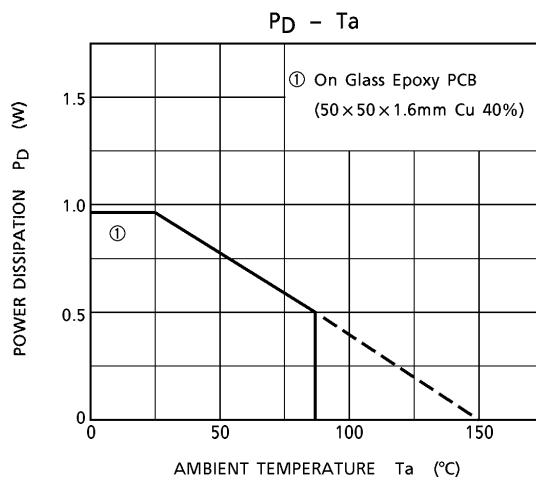
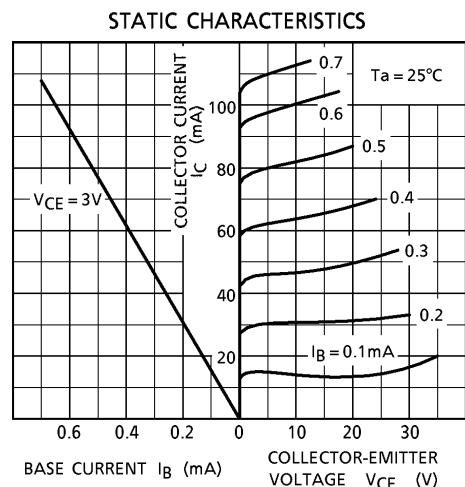
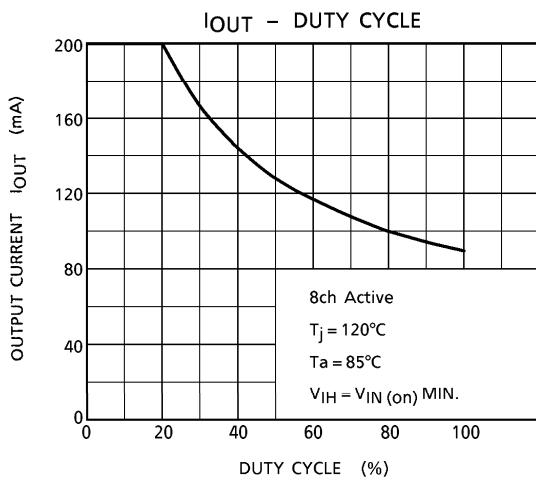
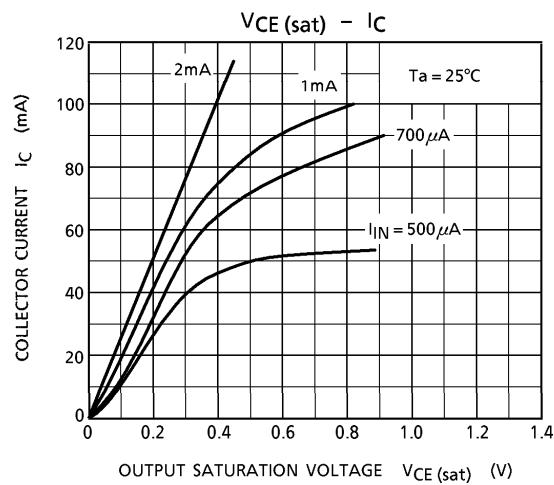
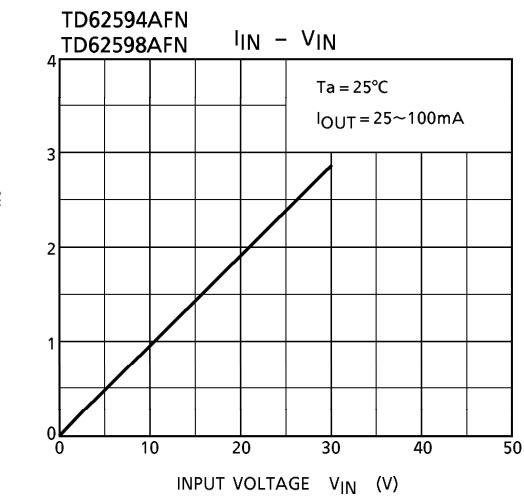
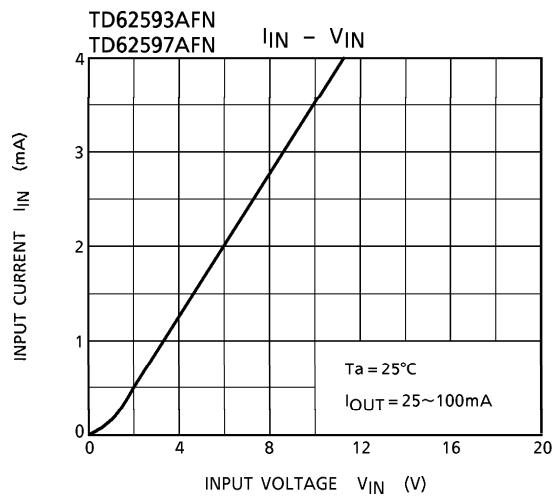
Input Condition

Type	R_{IN}	V_{IH}
TD62593AFN, TD62597AFN	0Ω	3V
TD62594AFN, TD62598AFN	0Ω	10V

(Note 3) CL includes probe and jig capacitance

PRECAUTIONS for USING

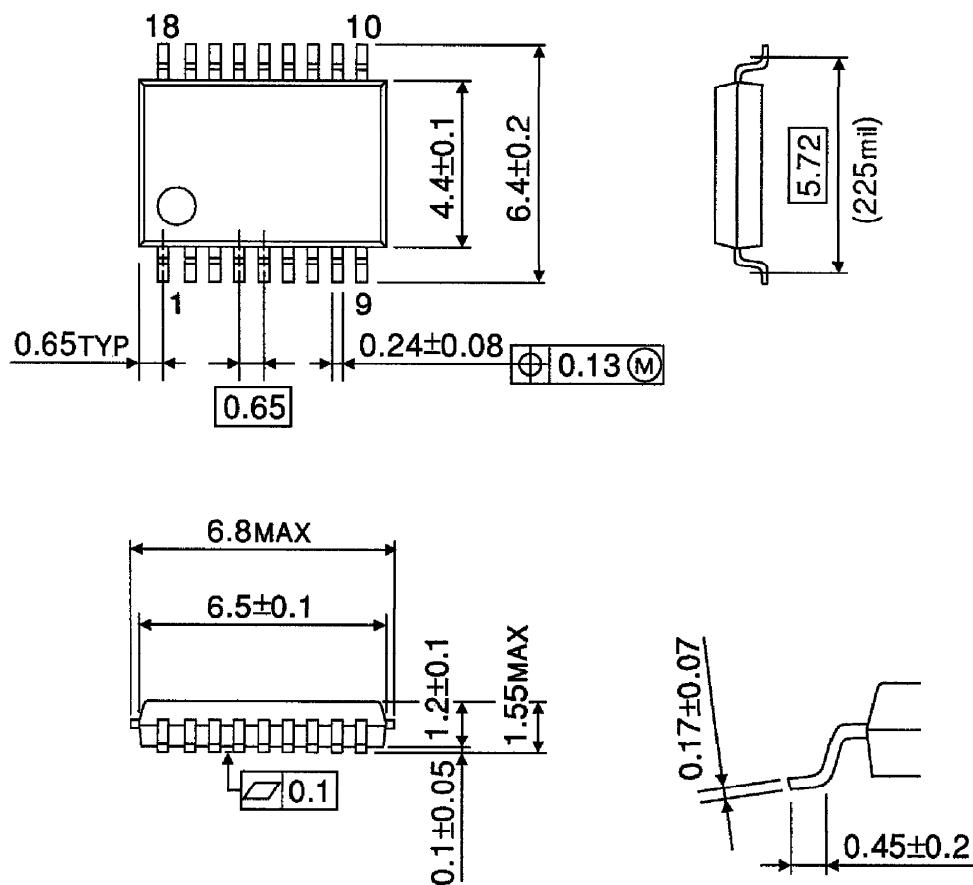
Utmost care is necessary in the design of the output line, V_{CC} and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.



OUTLINE DRAWING

SSOP18-P-225-0.65

Unit : mm



Weight : 0.09g (Typ.)